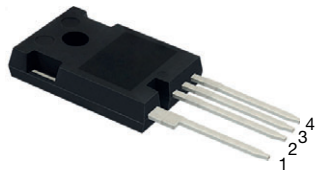
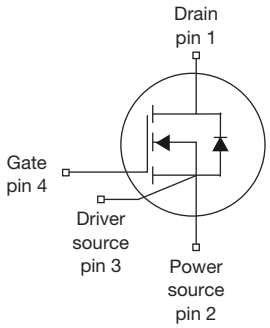
MaxSiC® 1200 V N-Channel SiC MOSFET

TO-247AD 4L





Marking Code: 120A160SL

FEATURES

- Fast switching speed
- Short circuit withstand time 2.5 µs
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Solar inverters
- Energy storage systems
- UPS (uninterruptible power supplies)

PRODUCT SUMMARY		
V_{DS} (V) at T_J max.	1200	
$R_{DS(on)}$ typ. (mΩ) at 25 °C	V_{GS} = 18 V	160
Q_g typ. (nC)	25	
I_D (A)	18	
C_{oss} typ. (pF)	31	
P_D (W)	109	
Configuration	Single	

ORDERING INFORMATION	
Package	TO-247AD 4L
Lead (Pb)-free and halogen-free	MXP120A160SL-GE3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	1200	V
Gate-source voltage		V_{GS}	-10 / +22	
Recommended operation voltage of gate-source		V_{GSOP}	-5 to -3 / +18	
Continuous drain current	T_C = 25 °C	I_D	18	A
Pulsed drain current [a]		I_{DM}	36	
Short-circuit withstand time [b]		T_{SC}	2.5	µs
Maximum power dissipation	T_C = 25 °C	P_D	109	W
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature)	For 10 s		260	°C
Single pulse avalanche energy [c]		E_{AS}	25	mJ

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature
b. V_{GS} = 18 V, V_{DS} = 800 V, $R_{g(ext)}$ = 20 Ω, verified by the design / characterization
c. T_J = 25 °C, V_{DD} = 120 V, L = 1 mH, V_{GS} = 18 V, I_{AS} = 7 A, verified by the design / characterization

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THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	40	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	1.37	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 1 mA		1200	-	-	V
Gate-source threshold voltage (N)	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 1.4 mA		-	3.1	-	V
		V_{DS} = V_{GS}, I_D = 1.4 mA, T_J = 175 °C		-	2.0	-	V
Gate-source leakage	I_{GSS}	V_{GS} = 22 V, V_{DS} = 0 V		-	-	100	nA
		V_{GS} = -10 V, V_{DS} = 0 V		-	-	-100	
Zero gate voltage drain current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = 0 V		-	-	10	µA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} = 15 V, I_D = 7 A		-	199	249	mΩ
		V_{GS} = 18 V, I_D = 7 A		-	160	200	
		V_{GS} = 18 V, I_D = 7 A, T_J = 175 °C		-	272	-	
Transconductance	gfs	V_{DS} = 10 V, I_D = 7 A		-	3	-	S
Dynamic							
Input capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 800 V, f = 100 KHz		-	713	-	pF
Output capacitance	C_{oss}			-	31	-	
Reverse transfer capacitance	C_{rss}			-	1	-	
Total gate charge	Q_g	V_{GS} = -5 V ~ 18 V, I_D = 7 A, V_{DS} = 800 V		-	25	-	nC
Gate-source charge	Q_{gs}			-	6	-	
Gate-drain charge	Q_{gd}			-	4	-	
Gate Resistance	R_g	V_{DS} = 0 V, f = 1 MHz		-	4	-	Ω
Switching Characteristics							
Turn-on delay time	$t_{d(on)}$	V_{GS} = -5 V ~ 18 V, I_D = 7 A, V_{DS} = 800 V, $R_{g(ext)}$ = 4.4 Ω	T_J = 25 °C	-	10	-	ns
			T_J = 175 °C	-	9	-	
Rise time	t_r		T_J = 25 °C	-	10	-	
			T_J = 175 °C	-	9	-	
Turn-off delay time	$t_{d(off)}$		T_J = 25 °C	-	12	-	
			T_J = 175 °C	-	12	-	
Fall time	t_f		T_J = 25 °C	-	14	-	
			T_J = 175 °C	-	13	-	
Turn-on switching energy	E_{on}		T_J = 25 °C	-	61	-	µJ
			T_J = 175 °C	-	55	-	
Turn-off switching energy	E_{off}		T_J = 25 °C	-	24	-	
			T_J = 175 °C	-	18	-	
Body Diode Ratings and Characteristic							
Forward diode voltage	V_{SD}	V_{GS} = -5 V, I_{SD} = 3.5 A, T_J = 25 °C		-	4.7	-	V
Continuous diode forward current	I_{SD}	V_{GS} = -5 V, T_J = 25 °C		-	-	16	A
Pulsed diode forward current	I_{SDM}			-	-	36	
Reverse recovery time	t_{rr}	V_{GS} = -5 V, I_{SD} = 7 A, V_R = 800 V, di/dt = 1000 A/µs		-	17	-	ns
Reverse recovery charge	Q_{rr}			-	29	-	nC
Reverse recovery current	I_{RRM}			-	3	-	A

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

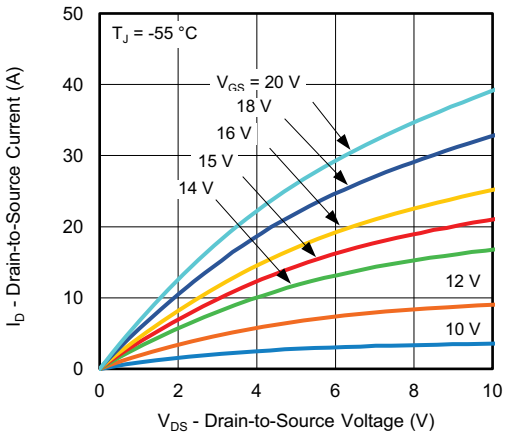

Fig. 1 - Typical Output Characteristics

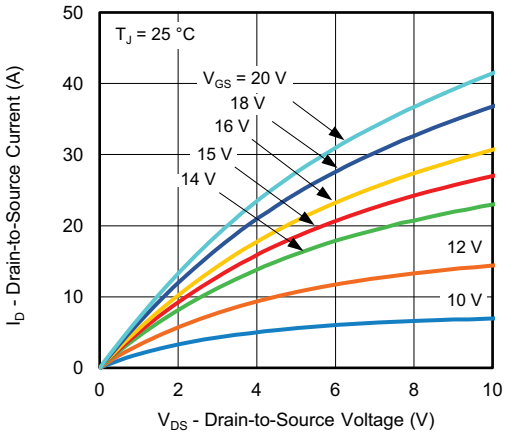

Fig. 2 - Typical Output Characteristics

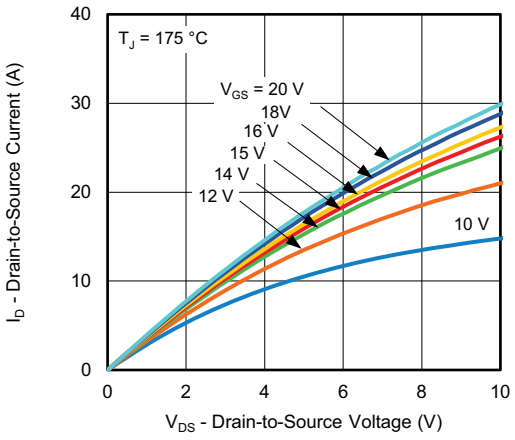

Fig. 3 - Typical Output Characteristics

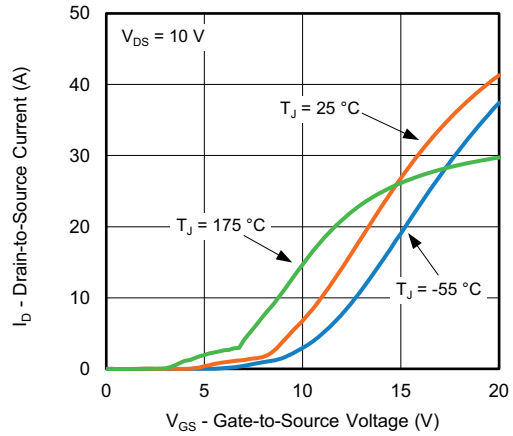

Fig. 4 - Typical Transfer Characteristics

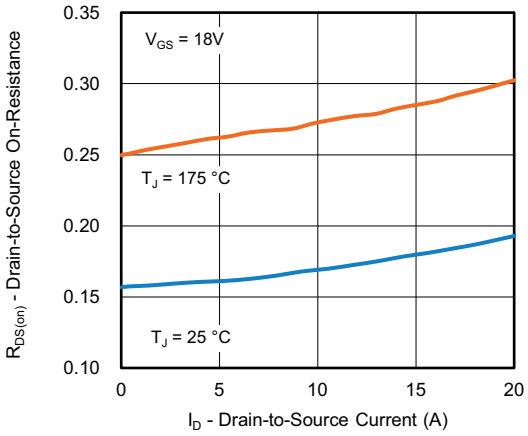

Fig. 5 - Normalized On-Resistance vs. Drain Current

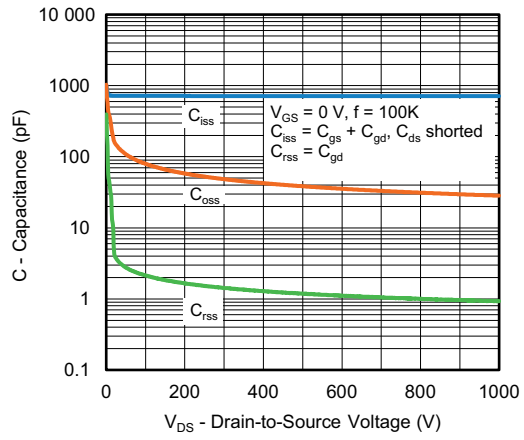

Fig. 6 - Typical Capacitance vs. Drain-to-Source Voltage

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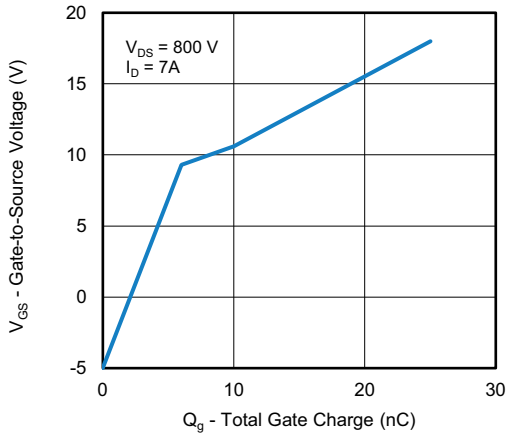

Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

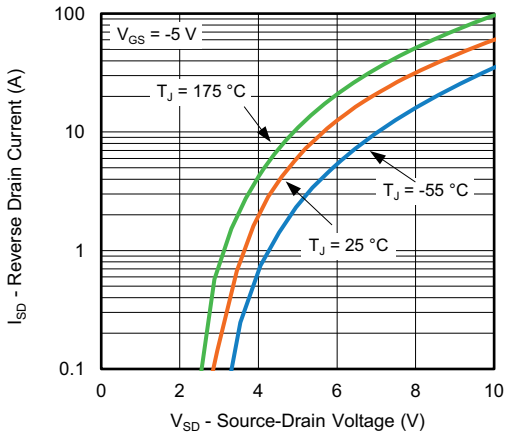

Fig. 10 - Typical Source-Drain Diode Forward Voltage

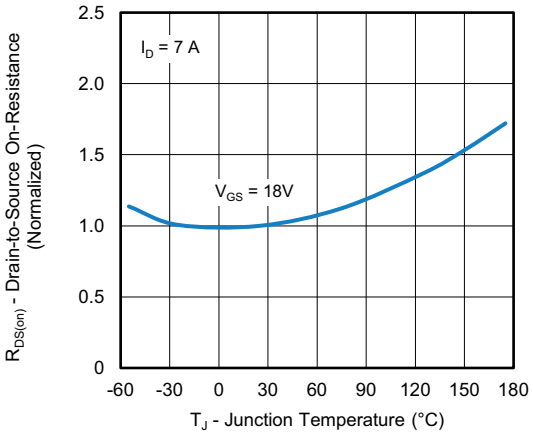

Fig. 8 - Normalized On-Resistance vs. Temperature

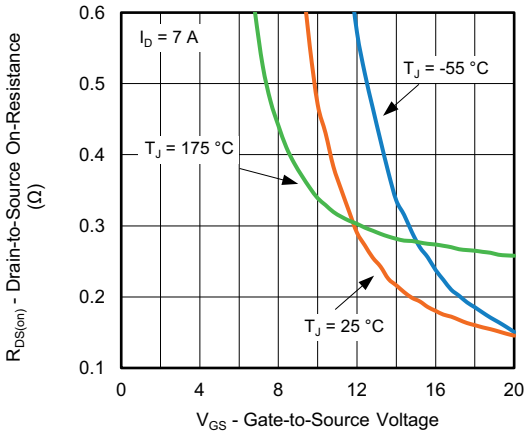

Fig. 11 - On-Resistance vs. Gate-to-Source Voltage

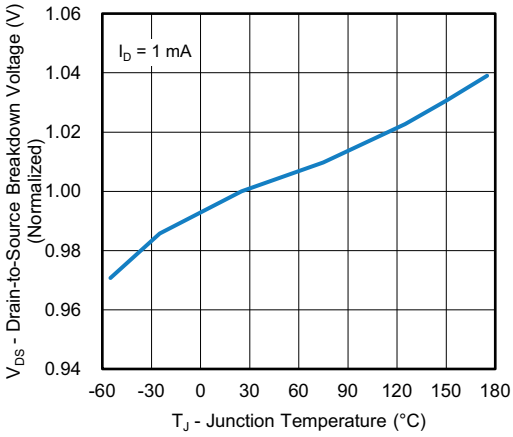

Fig. 9 - Drain-to-Source Voltage vs. Temperature

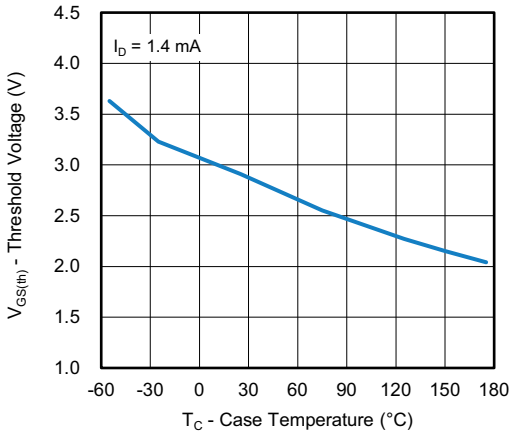

Fig. 12 - Threshold Voltage vs. Case Temperature

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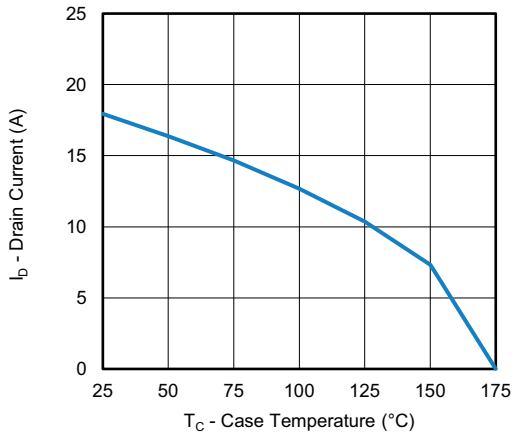

Fig. 13 - Drain Current vs. Case Temperature

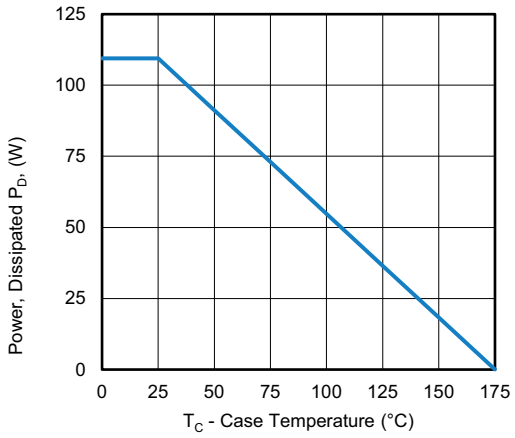

Fig. 14 - Output Capacitance and its Stored Energy vs. Drain-to-Source Voltage

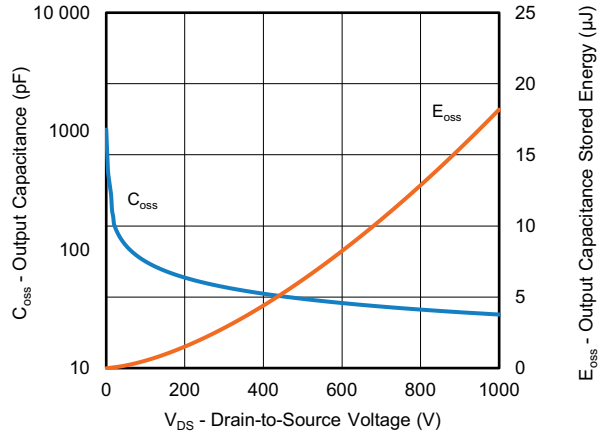

Fig. 15 - Power, Dissipated P_D vs. Case Temperature

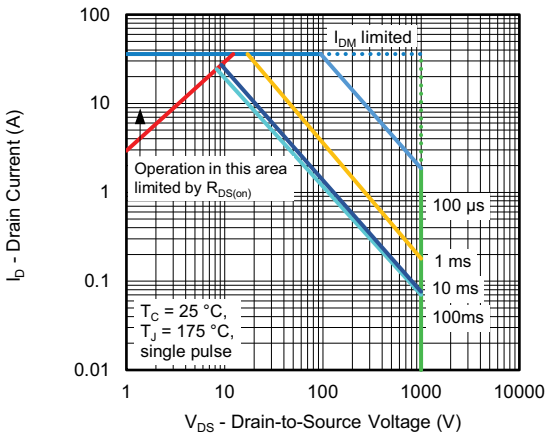

Fig. 16 - Safe Operating Area

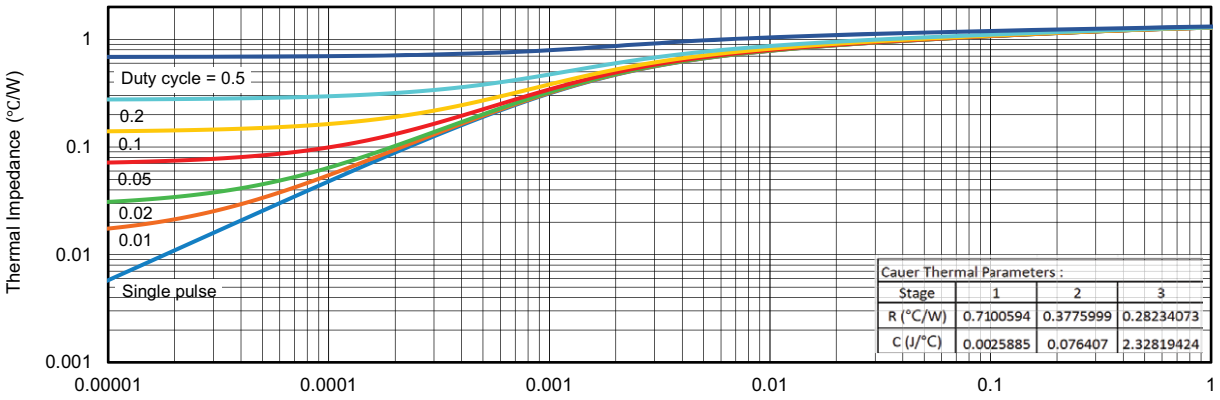

Fig. 17 - Transient Thermal Impedance

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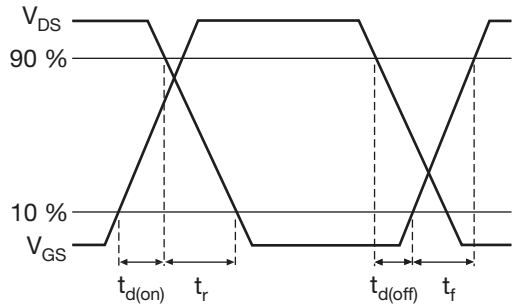

Fig. 18 - Waveforms of Switching Time

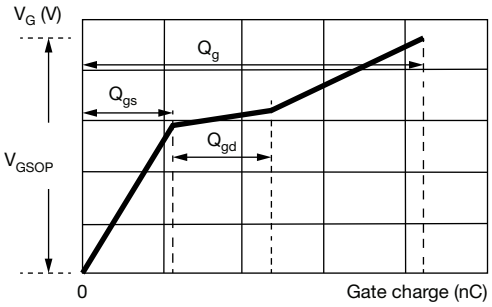

Fig. 21 - Waveforms for Gate Charge

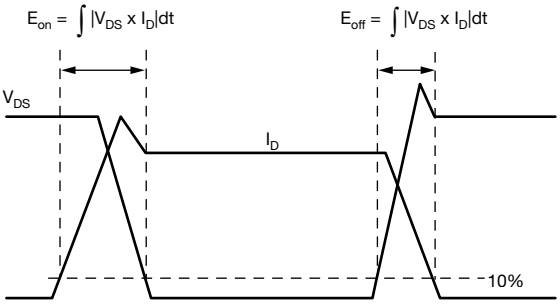

Fig. 19 - Waveforms for Switching Energy

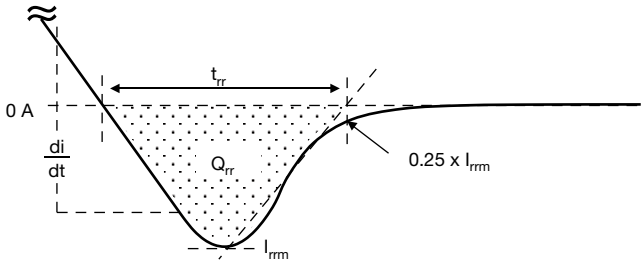

Fig. 22 - Waveforms for Reverse Recovery

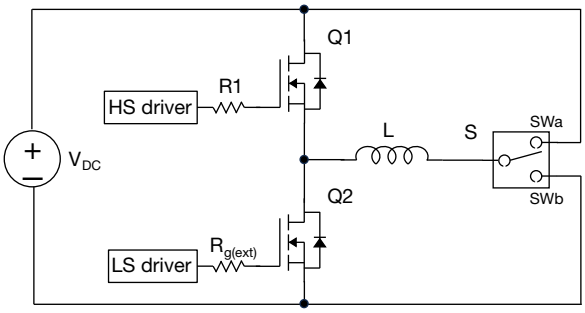

Fig. 20 - Switching and Reverse Diode Characteristics Measurement Circuit

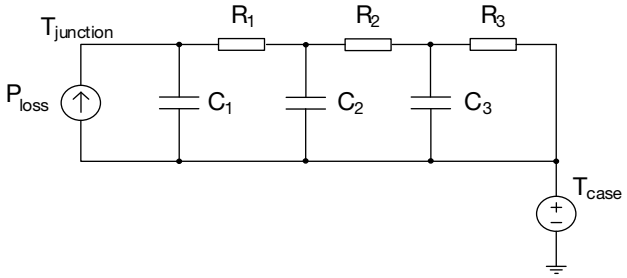

Fig. 23 - Thermal Equivalent Circuit

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